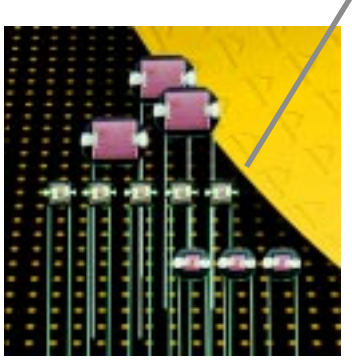
Photocells A 9050, A 9060

Epoxy encapsulated series

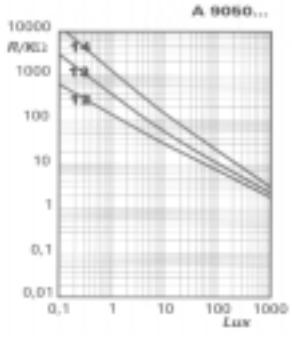


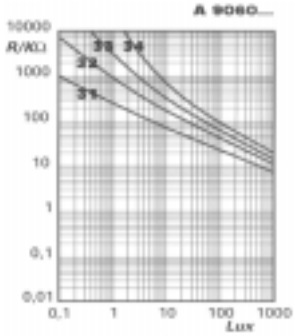
Light Switch Appliactions

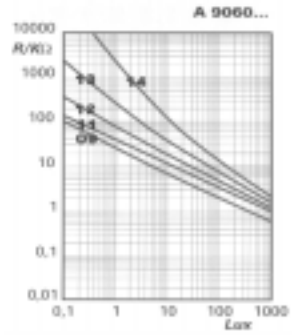
Indoor and Outdoor

This Photocell series includes two different spectral sensitivity ranges. The A90... range is the smallest size of photocell in epoxy encapsulation. Customized selections are available upon request.

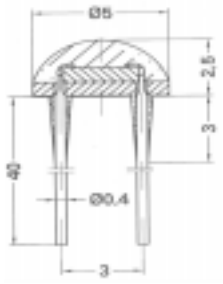
Operating Temperature Range: -20...+80 °C (non continuous)
Storage Temperature Range: -20...+80 °C (non continuous)

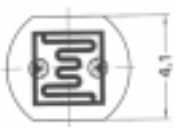






Type	R_{10}	R_{100}	R_{01}	R_{05}	V_{max}	P_{max}	$\gamma_{10/100}$	λ_{peak}
units	KΩ	KΩ typ.	MΩ min	MΩ min	V	mW	typ.	nm
A 9060 09	4...11	2	0,04	0,12	100	90	0,65	600
A 9060 11	9...20	3,5	0,06	0,18	150	90	0,65	600
A 9060 12	16...33	5	0,18	0,5	150	90	0,7	600
A 9060 13	27...94	8	0,5	1,5	150	90	0,8	600
A 9060 14	77...340	15	1,5	5,0	150	90	0,9	600
A 9060 31	60...130	23	0,4	1,2	300	90	0,65	600
A 9060 32	120...210	35	1,0	3,0	300	90	0,7	600
A 9060 33	200...580	50	3,0	9	300	90	0,8	600
A9060 34	500...1200	100	5,0	15	300	90	0,9	600
A 9050 12	18...44	7	0,15	0,45	150	90	0,65	530
A 9050 13	36...88	12	0,4	1,2	150	90	0,7	530
A 9050 14	70...200	20	1,0	3,0	150	90	0,75	530





all Dimensions in mm

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Singapore 139947
Phone +65 775 2022
Fax +65 775 1008

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SPECIFICATION
FOR
OPTO - SENSORS

Customer :	
Representative :	
Type :	**A9013**
PerkinElmer Part No. :	**95503651**
Date :	**2005.11.30**

This specification has been provided by R &D Department of PerkinElmer Optoelectronics

No. of Samples :	**NA**
Technical Data :	**4 pages**

The undersigned hereby confirm that PerkinElmer quality assurance system has been applied to the shipment this specification is attached to. All devices have met the requirements of PerkinElmer test specifications and passed a 100% final production test plus a sample lot outgoing inspection in accordance with GB/T 2828.1-2003/ISO 2859-1: 1999.

CHECKED :	APPROVED : William Wang 2005.11.30

Customer Approval : Date Signature

IN CASE OF SAMPLES ACCEPTANCE ; PLEASE ATTACH THE SIGNED FRONT PAGE OF THIS SPECIFICATION TO YOUR KIND ORDER

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SPECIFICATION
FOR
OPTO - SENSORS

Type : A9013

x	Standard Type		Customer Specific Type

The marked test criteria have been applied to the attached samples and will be implemented as 100% test at final assembly. Below typical characteristic data are provided for reference.

	R	1	*Resistance value at 1 lux (0.093 fc)*	:		kΩ
x	R	10	*Resistance value at 10 lux (0.93 fc)*	:	27 – 94	kΩ
	R	100	*Resistance value at 100 lux (9.3 fc)*	:		kΩ
	R		*Resistance value as stated besides*	:		kΩ
x	R_0	1	*Minimum Resistance 1 sec after removal from light*	:	0.5	MΩ
	R_0	5	*Minimum Resistance 5 sec after removal from light*	:		MΩ
	R_0		*Minimum Resistance after dark time stated besides*	:		MΩ
	γ		*Slope as given by* $\frac{lg(R10/R100)}{lg(100/10)}$ *typ.*	:		

LIMIT VALUES			
Maximum Power Dissipation	:	90	mW
Maximum Supply Voltage (DC or AC_{pk})	:	150	V
Temperature Coefficient	:	0.4	%/°C
Peak Spectral Response	:	600±20	nm

ENCAPSULATION

	Hermetically Sealed Metal Case
	Hermetically Sealed Glass Bulb
x	Epoxy Coating
	Lacquer Coating

Date	2005.11.30	Signature	William Wang

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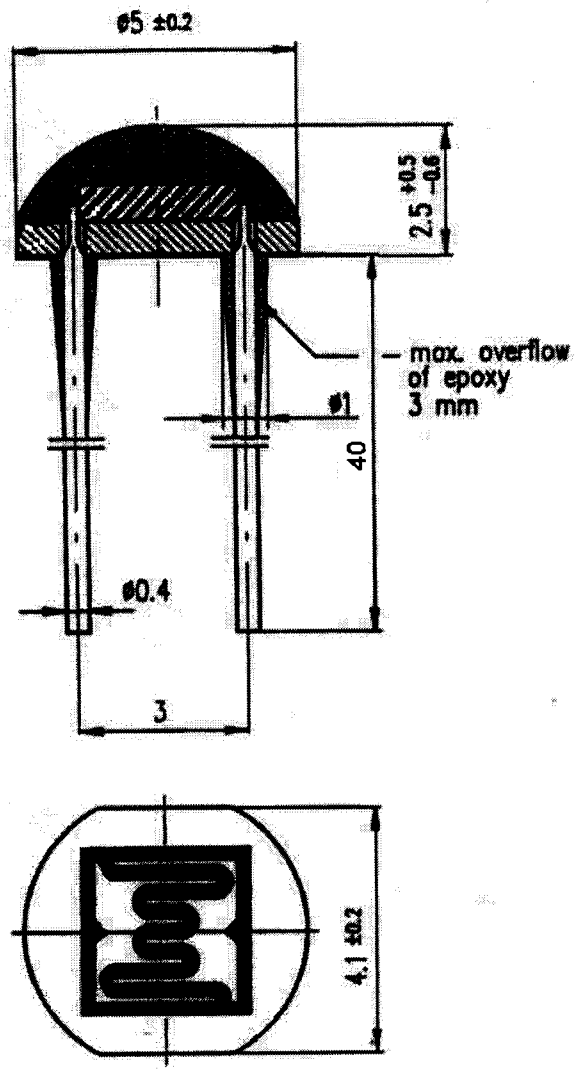
SPECIFICATION
FOR
OPTO - SENSORS

Type : A9013

Mechanical Drawing

PACKAGE DIMENSIONS mm



Date	Signature
2005.11.29	William Wang

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SPECIFICATION
FOR
OPTO - SENSORS

COMMON INFORMATIONS

PerkinElmer Photoconductive Cells pass a 100% final electrical test, consisting light readings at defined light level(s) and dark resistance R_0 taken at certain sec after switch off of an illumination as specified. Additionally an outgoing test according to GB/T 2828.1-2003/ISO 2859-1: 1999 is applied to all shipments. Prior to measurements, all devices are exposed to normal room light (approx. 500 lux) for at least 16 hours. This preconditioning compensates the effect of "light history", a typical reaction of this kind of semiconductive component, leading usually to an adaption of resistance value to its preillumination within a certain range. If no special procedure is required , all readings are taken under a tungsten filament light source being run at 2854 ± 50 K color temperature. Dark resistance readings are achieved at the defined time after covering the light source with an electromagnetic shutter within 10 msec.

LONG TIME STABILITY

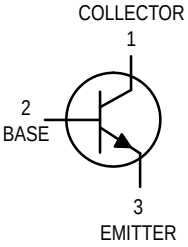
is influenced by light history effect as well. Stability of light readings will be guaranteed in case of approximately equal intervals of bright and dark ambient conditions. In case of application of only singular light condition an increase of typical readings has to be expected in case of high ambient light, a decrease in case of long dark period. The absolute variation will be within ± 10% at 10 lux with tendencily higher deviation at lower light levels.

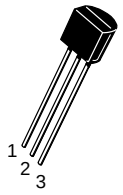
STORAGE AND HANDLING

All PerkinElmer photoconductive cells are subjected to an artificial aging cycle consisting various combinations of illumination and temperature for a certain time.This aging guarantees constancy of light reaings at ambient temperatures up to 70°C within the announced temperature coefficient range. Recommended storage conditions are temperatures beneath 60°C and usual moisture of approximately 50% r.H. Through soldering process a preheating of components surface exceeding 130°C should be avoided. Automatic soldering shouldn't last more than 10 seconds at 260°C. Otherwise a stand off of 5 mm should be applied.

Amplifier Transistors
NPN Silicon

BC546, B
BC547, A, B, C
BC548, A, B, C





CASE 29–04, STYLE 17
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	BC 546	BC 547	BC 548	Unit
Collector–Emitter Voltage	V_{CEO}	65	45	30	Vdc
Collector–Base Voltage	V_{CBO}	80	50	30	Vdc
Emitter–Base Voltage	V_{EBO}	6.0			Vdc
Collector Current — Continuous	I_C	100			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12			Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I_C = 1.0 mA, I_B = 0)	BC546 BC547 BC548	$V_{(BR)CEO}$	65 45 30	— — —	— — —	V
Collector–Base Breakdown Voltage (I_C = 100 μAdc)	BC546 BC547 BC548	$V_{(BR)CBO}$	80 50 30	— — —	— — —	V
Emitter–Base Breakdown Voltage (I_E = 10 μA, I_C = 0)	BC546 BC547 BC548	$V_{(BR)EBO}$	6.0 6.0 6.0	— — —	— — —	V
Collector Cutoff Current (V_{CE} = 70 V, V_{BE} = 0) (V_{CE} = 50 V, V_{BE} = 0) (V_{CE} = 35 V, V_{BE} = 0) (V_{CE} = 30 V, T_A = 125°C)	 BC546 BC547 BC548 BC546/547/548	I_{CES}	 — — — —	 0.2 0.2 0.2 —	 15 15 15 4.0	 nA μA

REV 1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				—
(I_C = 10 μA, V_{CE} = 5.0 V)	BC547A/548A		—	90	—	
	BC546B/547B/548B		—	150	—	
	BC548C		—	270	—	
(I_C = 2.0 mA, V_{CE} = 5.0 V)	BC546		110	—	450	
	BC547		110	—	800	
	BC548		110	—	800	
	BC547A/548A		110	180	220	
	BC546B/547B/548B		200	290	450	
	BC547C/BC548C		420	520	800	
(I_C = 100 mA, V_{CE} = 5.0 V)	BC547A/548A		—	120	—	
	BC546B/547B/548B		—	180	—	
	BC548C		—	300	—	
Collector–Emitter Saturation Voltage		$V_{CE(sat)}$				V
(I_C = 10 mA, I_B = 0.5 mA)			—	0.09	0.25	
(I_C = 100 mA, I_B = 5.0 mA)			—	0.2	0.6	
(I_C = 10 mA, I_B = See Note 1)			—	0.3	0.6	
Base–Emitter Saturation Voltage		$V_{BE(sat)}$	—	0.7	—	V
(I_C = 10 mA, I_B = 0.5 mA)						
Base–Emitter On Voltage		$V_{BE(on)}$				V
(I_C = 2.0 mA, V_{CE} = 5.0 V)			0.55	—	0.7	
(I_C = 10 mA, V_{CE} = 5.0 V)			—	—	0.77	
SMALL–SIGNAL CHARACTERISTICS						
Current–Gain — Bandwidth Product		f_T				MHz
(I_C = 10 mA, V_{CE} = 5.0 V, f = 100 MHz)	BC546		150	300	—	
	BC547		150	300	—	
	BC548		150	300	—	
Output Capacitance		C_{obo}	—	1.7	4.5	pF
(V_{CB} = 10 V, I_C = 0, f = 1.0 MHz)						
Input Capacitance		C_{ibo}	—	10	—	pF
(V_{EB} = 0.5 V, I_C = 0, f = 1.0 MHz)						
Small–Signal Current Gain		h_{fe}				—
(I_C = 2.0 mA, V_{CE} = 5.0 V, f = 1.0 kHz)	BC546		125	—	500	
	BC547/548		125	—	900	
	BC547A/548A		125	220	260	
	BC546B/547B/548B		240	330	500	
	BC547C/548C		450	600	900	
Noise Figure		NF				dB
(I_C = 0.2 mA, V_{CE} = 5.0 V, R_S = 2 kΩ,	BC546		—	2.0	10	
f = 1.0 kHz, Δf = 200 Hz)	BC547		—	2.0	10	
	BC548		—	2.0	10	

Note 1: I_B is value for which I_C = 11 mA at V_{CE} = 1.0 V.

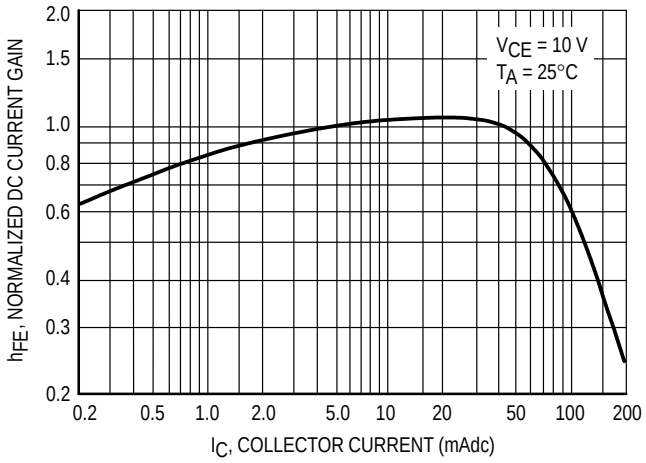


Figure 1. Normalized DC Current Gain

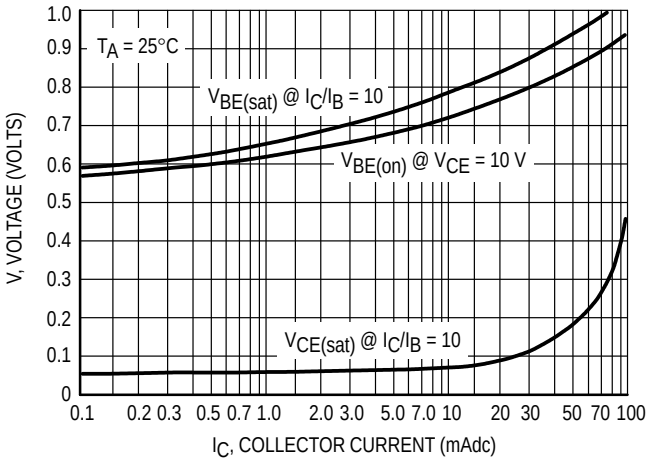


Figure 2. "Saturation" and "On" Voltages

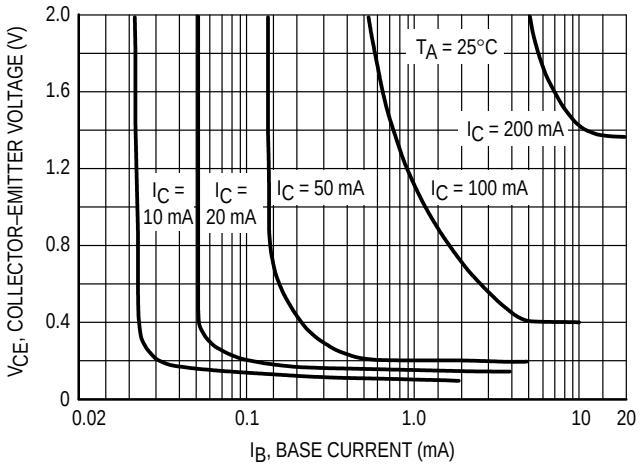


Figure 3. Collector Saturation Region

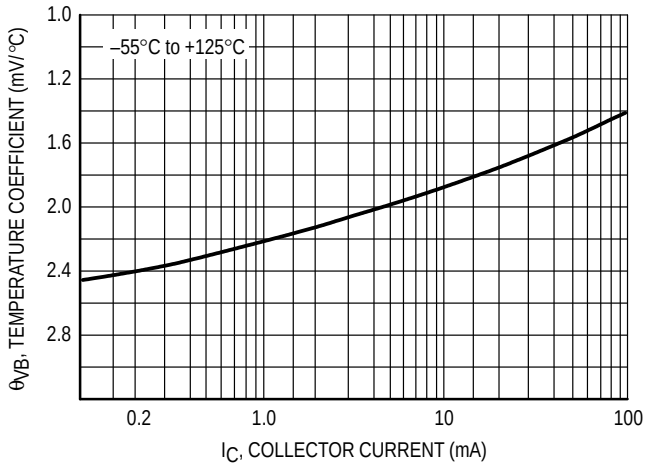


Figure 4. Base–Emitter Temperature Coefficient

BC547/BC548

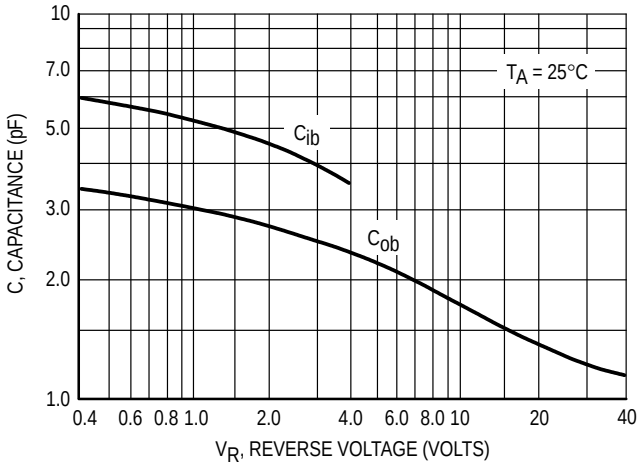


Figure 5. Capacitances

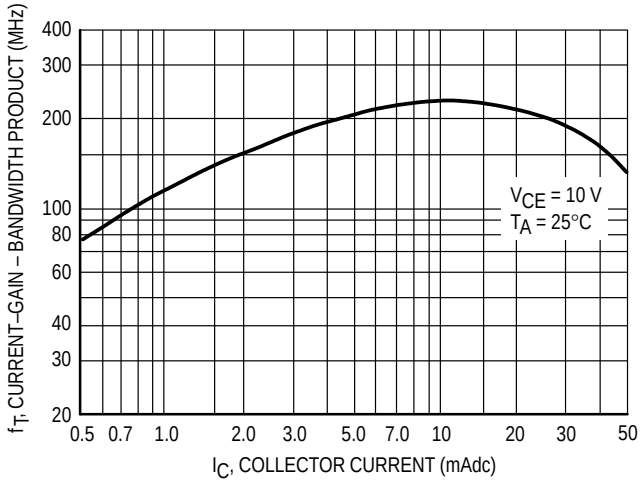


Figure 6. Current–Gain – Bandwidth Product

BC547/BC548

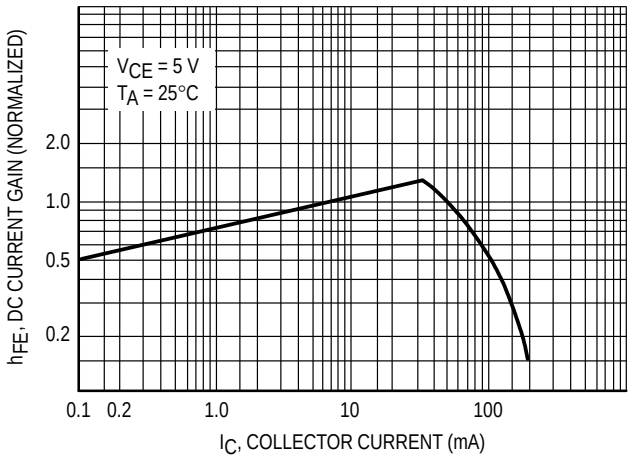


Figure 7. DC Current Gain

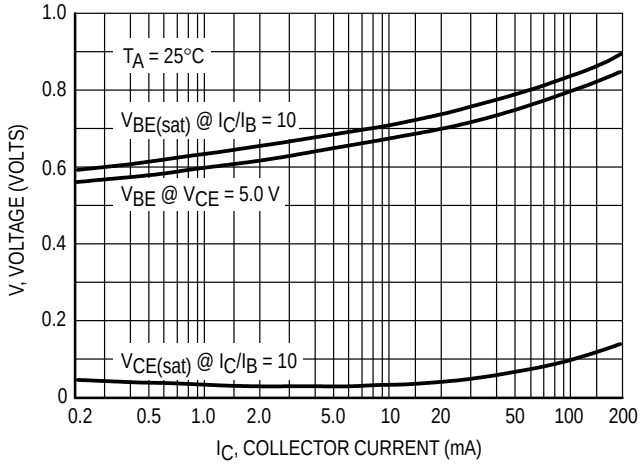


Figure 8. “On” Voltage

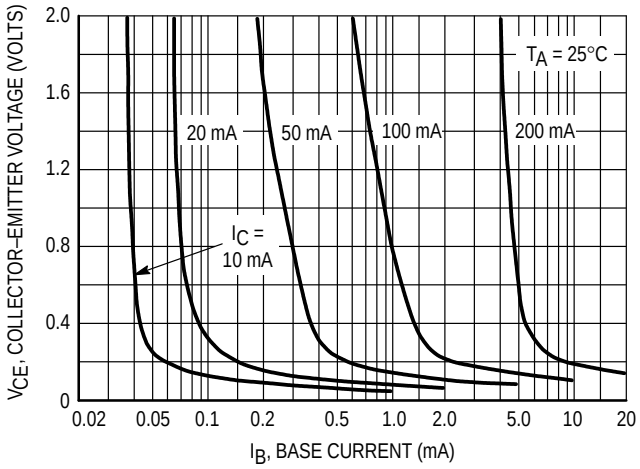


Figure 9. Collector Saturation Region

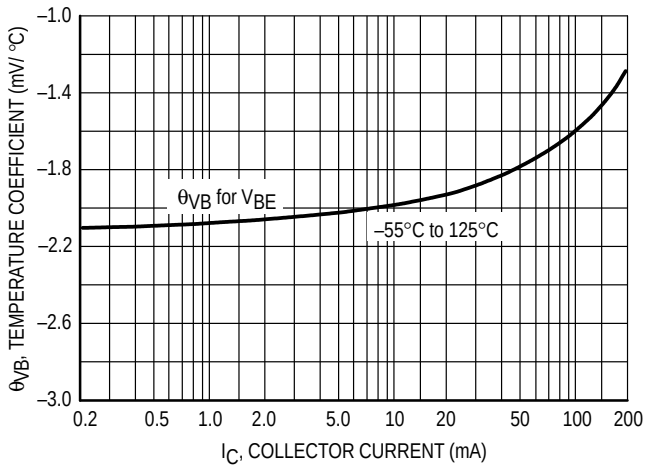


Figure 10. Base–Emitter Temperature Coefficient

BC546

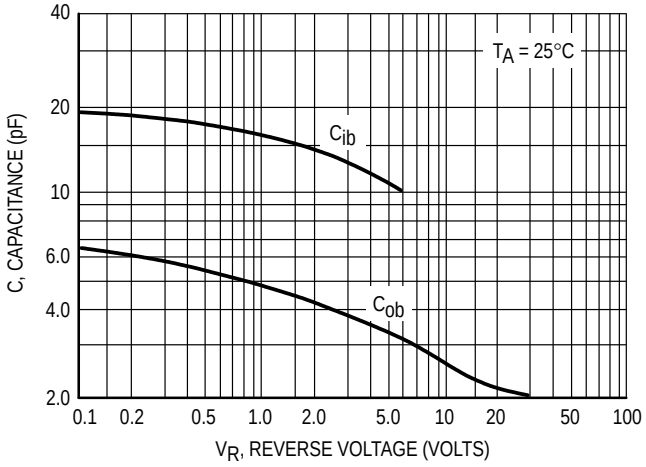


Figure 11. Capacitance

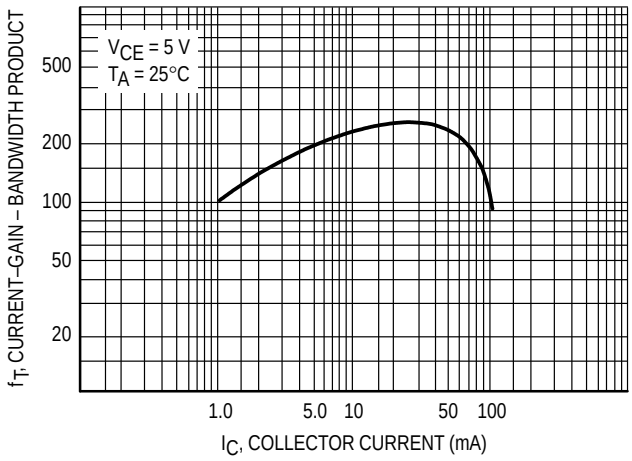
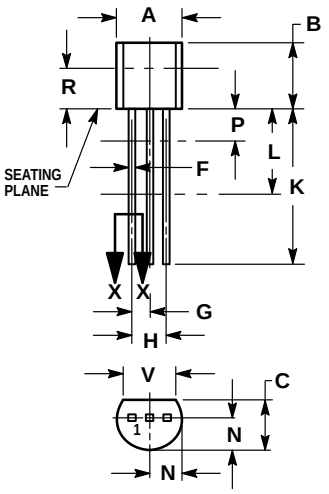
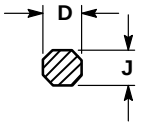


Figure 12. Current–Gain – Bandwidth Product

PACKAGE DIMENSIONS





SECTION X–X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

CASE 029–04
(TO–226AA)
ISSUE AD

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

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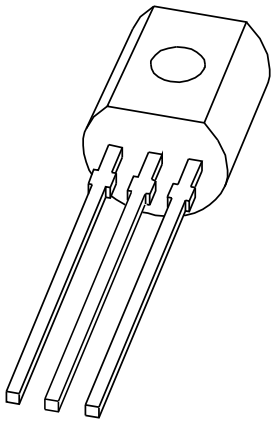
JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki,
6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298

DATA SHEET



BC556; BC557; BC558
PNP general purpose transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Mar 27

Philips
Semiconductors

PHILIPS

PNP general purpose transistors BC556; BC557; BC558

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a TO-92; SOT54 plastic package.
NPN complements: BC546, BC547 and BC548.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector

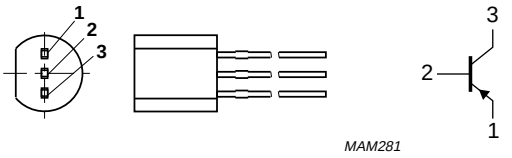


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC556		–	–80	V
	BC557		–	–50	V
	BC558		–	–30	V
V_{CEO}	collector-emitter voltage	open base			
	BC556		–	–65	V
	BC557		–	–45	V
	BC558		–	–30	V
I_{CM}	peak collector current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	500	mW
h_{FE}	DC current gain	$I_C = -2$ mA; $V_{CE} = -5$ V			
	BC556		125	475	
	BC557; BC558		125	800	
f_T	transition frequency	$I_C = -10$ mA; $V_{CE} = -5$ V; f = 100 MHz	100	–	MHz

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC556		–	–80	V
	BC557		–	–50	V
	BC558		–	–30	V
V_{CEO}	collector-emitter voltage	open base			
	BC556		–	–65	V
	BC557		–	–45	V
	BC558		–	–30	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

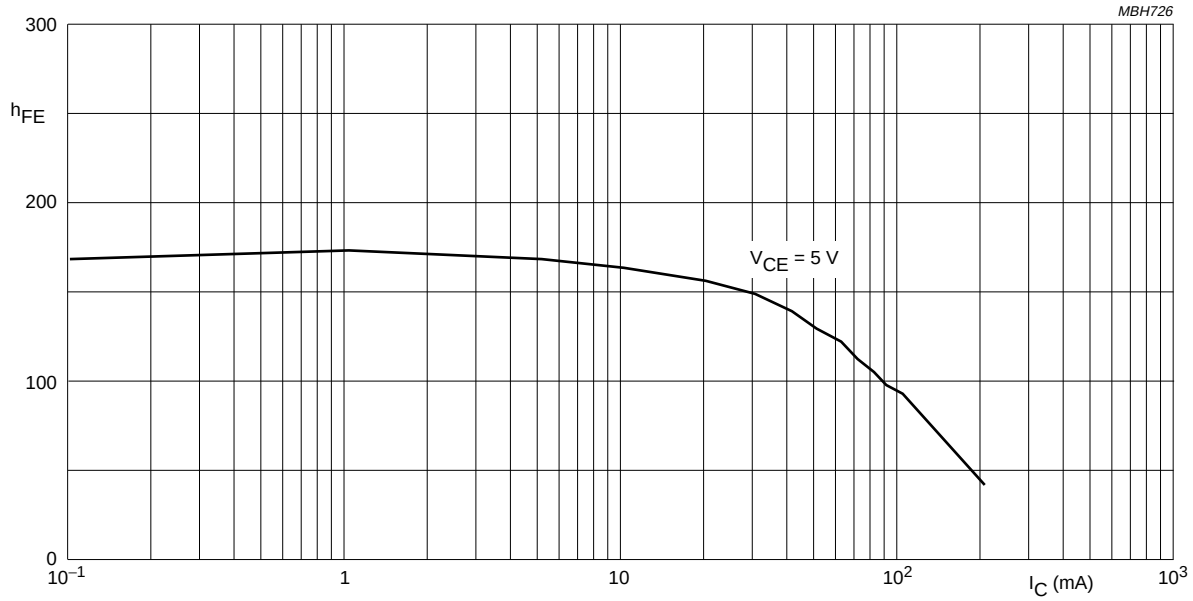
CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = –30 V	–	–1	–15	nA
		I_E = 0; V_{CB} = –30 V; T_j = 150 °C	–	–	–4	μA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = –5 V	–	–	–100	nA
h_{FE}	DC current gain	I_C = –2 mA; V_{CE} = –5 V; see Figs 2, 3 and 4				
	BC556		125	–	475	
	BC557; BC558		125	–	800	
	BC556A; BC557A; BC558A		125	–	250	
	BC556B; BC557B; BC558B		220	–	475	
	BC557C; BC558C		420	–	800	
V_{CEsat}	collector-emitter saturation voltage	I_C = –10 mA; I_B = –0.5 mA	–	–60	–300	mV
		I_C = –100 mA; I_B = –5 mA	–	–180	–650	mV
V_{BEsat}	base-emitter saturation voltage	I_C = –10 mA; I_B = –0.5 mA; note 1	–	–750	–	mV
		I_C = –100 mA; I_B = –5 mA; note 1	–	–930	–	mV
V_{BE}	base-emitter voltage	I_C = –2 mA; V_{CE} = –5 V; note 2	–600	–650	–750	mV
		I_C = –10 mA; V_{CE} = –5 V; note 2	–	–	–820	mV
C_c	collector capacitance	I_E = i_e = 0; V_{CB} = –10 V; f = 1 MHz	–	3	–	pF
C_e	emitter capacitance	I_C = i_c = 0; V_{EB} = –0.5 V; f = 1 MHz	–	10	–	pF
f_T	transition frequency	I_C = –10 mA; V_{CE} = –5 V; f = 100 MHz	100	–	–	MHz
F	noise figure	I_C = –200 μA; V_{CE} = –5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	–	2	10	dB

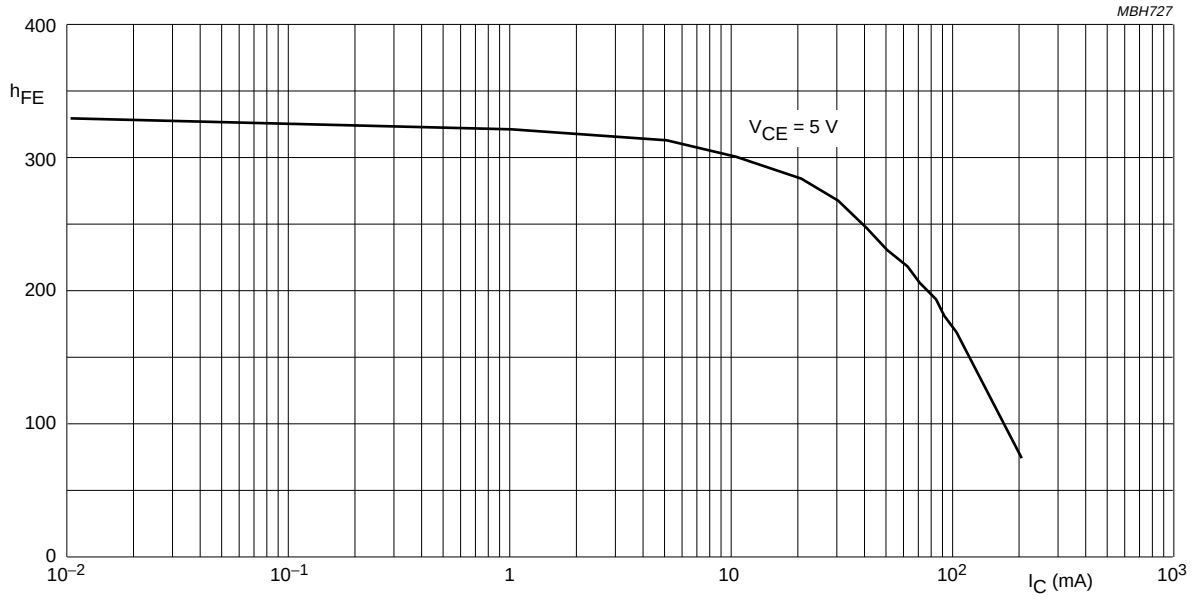
Notes

1. V_{BEsat} decreases by about –1.7 mV/K with increasing temperature.
2. V_{BE} decreases by about –2 mV/K with increasing temperature.



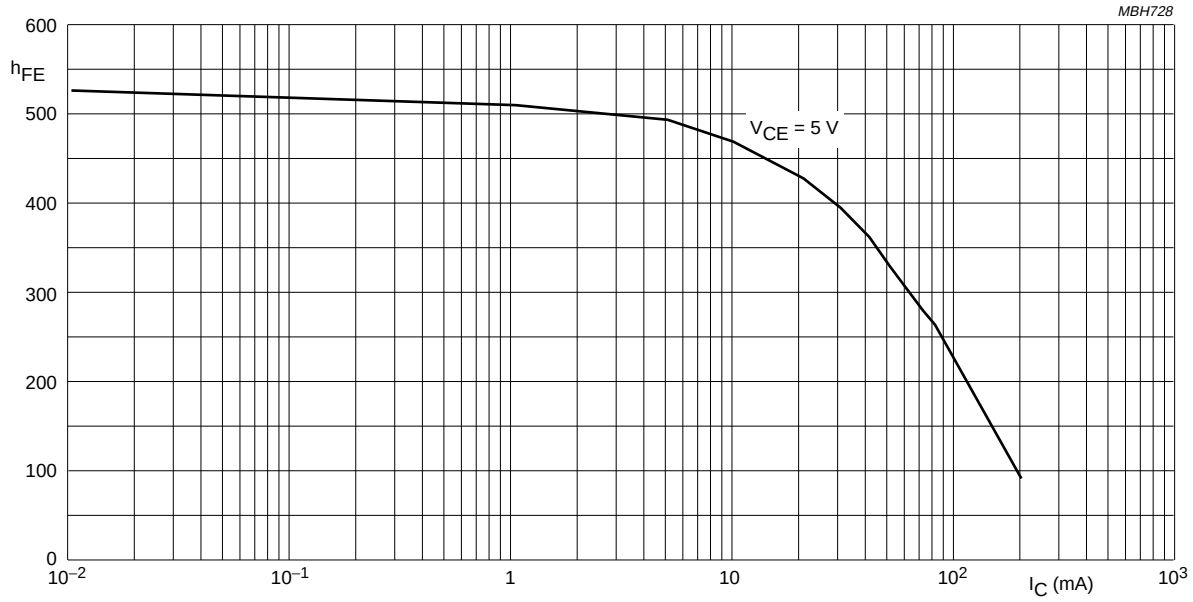
BC556A; BC557A; BC558A.

Fig.2 DC current gain; typical values.



BC556B; BC557B; BC558B.

Fig.3 DC current gain; typical values.

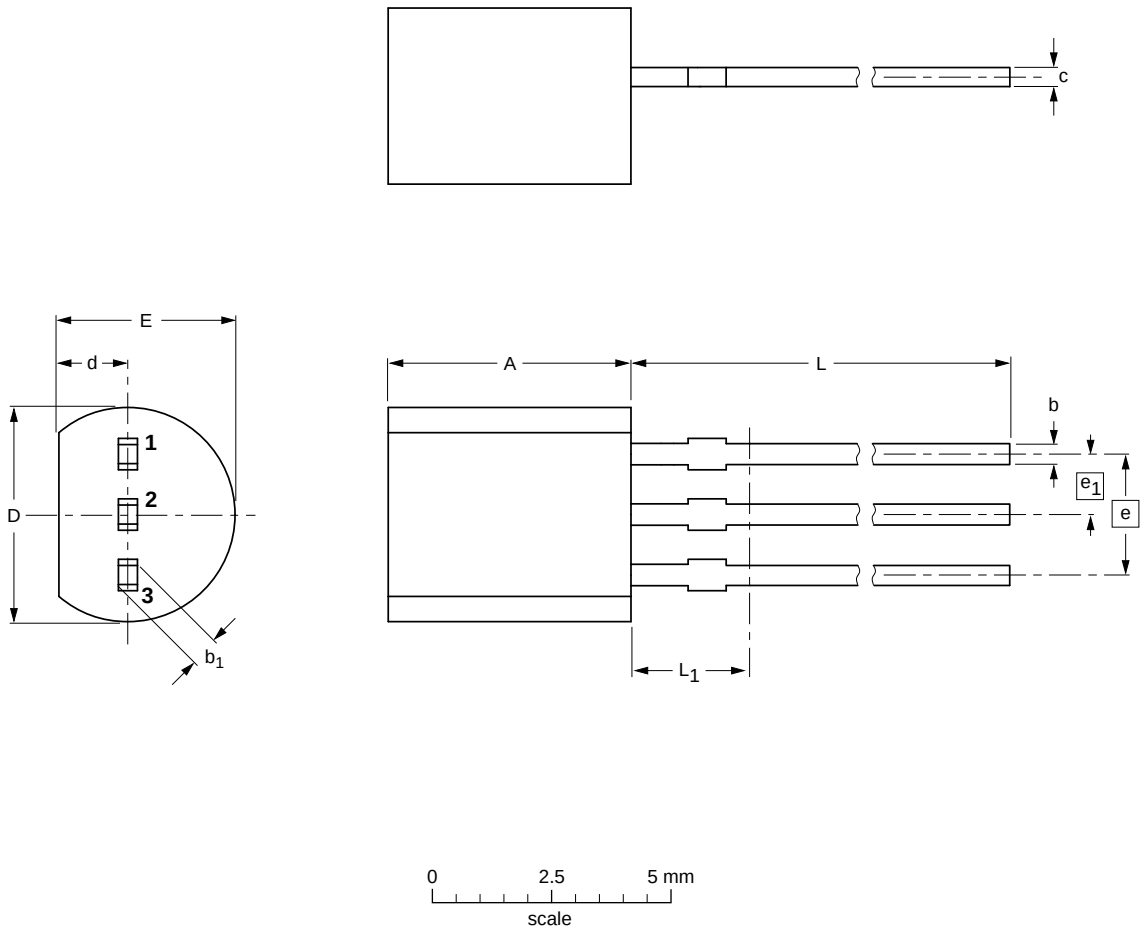


BC557C; BC558C.

Fig.4 DC current gain; typical values.

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1(1)
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT54		TO-92	SC-43			97-02-28

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NOTES

NOTES

NOTES

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Philips Semiconductors

PHILIPS

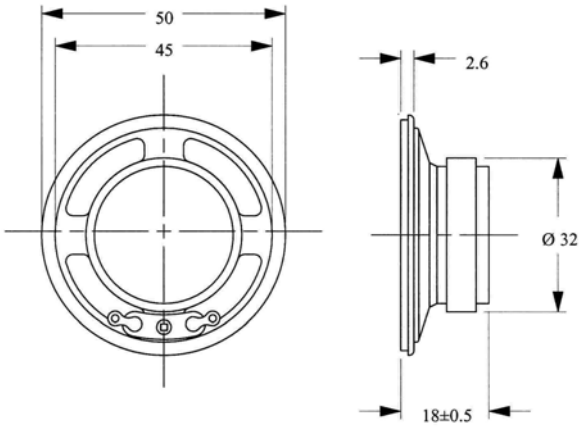
LSM-50M/F (Artikel-Nr. 335405-07)

EKULIT

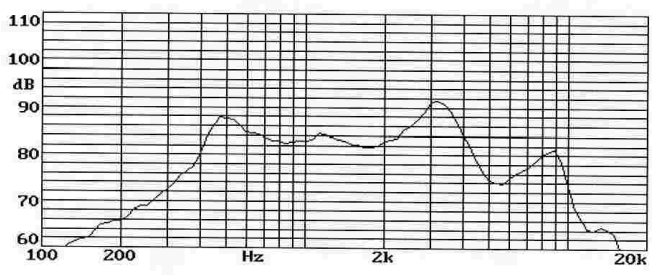
SPECIFICATIONS:

TYPE	UNIT	LSM-50M/F
Impedance	Ω	8±15%
Power (Nominal)	W	0.2
Power (Maximum)	W	0.4
Resonant Frequency	Hz	550±20%
Sound Pressure Level	dB	84±3
Frequency Range	Hz	Fo~4.500
Operating Temperature	°C	-20~+60
Storage Temperature	°C	-30~+70

DIMENSIONS :
(Unit: mm)



Frequency response:



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Tel: **+49-9604/40 89 88** • Fax: **+49-9604/40 89 36**
E-mail: **businessbetreuung@conrad.de** Web site: **www.CONRAD.de**

Einstellregler PT15 (15 mm Durchmesser)

KOHLESCHICHT

- Kein Hartpapier-Träger, sondern hochwertige Polyester-Folie; dadurch hervorragend hinsichtlich Feuchtigkeit und mechanischer Beanspruchung (keine Haarrisse).
- Volleingekapselte Gehäuse, die das Eindringen von Staub, Kolophonium und anderen umweltschädlichen Einflüssen verhindern.

Auf Anfrage:

- Auch als Drehschalter bzw. Umschalter verwendbar.
- Mittelrast.
- Lange mechanische Lebensdauer ($\geq$ 10.000 Zyklen) PTE 15 . . .
- Kunststoff selbstlöschend nach DIN UL-94 : V-0.
- Langloch für Steckachse um 90° verdreht (PT15 NG . . .
- Höhe 8,5 mm anstatt 7 mm Standard (PT15 NvA . . .)

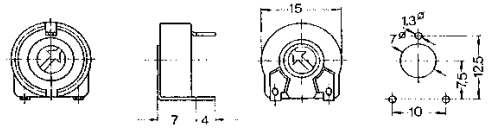
Mechanische und elektrische Eigenschaften

Drehwinkel mechanisch	265° ± 5°
Drehwinkel elektrisch	250° ± 20° (auf Anfrage: ± 2°)
Drehmoment gemessen bei 3-5 U/sec.	0,5 bis 2,5 Ncm
Anschlagfestigkeit	10 Ncm
Fertigungsbereich	100 Ω – 5 M Ω (Werte: 50 Ω und 10 M Ω auf Anfrage)
Toleranz	Werte: 100 Ω – 1 M Ω : ± 20 % / > 1 M Ω – 5 M Ω ± 30 % / 50 Ω und 10 M Ω : + 50 % – 30 % (Toleranz - Selektierung: Auf Anfrage)
Belastbarkeit	Tu 40° C / LIN: 0,25 W / LOG: 0,125 W
Grenzspannung V_R (V)	LIN: 250 V = / LOG: 200 V =
Kurvenformen	LIN, Pos. LOG, Neg. LOG (Kurven 1, 4 und 5 nach DIN 41450) (Kurven 4 und 5 ab 1 K Ω lieferbar)
Restwiderstand (nach DIN 41450)	LIN: $\leq$ 500 Ω : 2 Ω / > 500 Ω $\leq 5{:}10^{-3}$ R_N LOG: Anfang $\leq 1{:}10^{-3}$ R_N / Ende $\leq 2{:}10^{-2}$ R_N
Temperaturbereich	– 25 bis + 70° C
Widerstandsrauschen bei 10-15 U/sec.	$\leq$ 3 % des R_N oder 3 Ω
Übergangswiderstand	$\leq$ 5 % des R_N

Lieferbare Ausführungen ab Lager – Verpackungseinheit 200 Stück

KOHLESCHICHT

PT 15 Lv (12,5)



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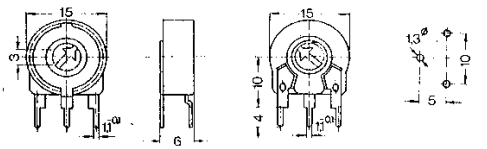
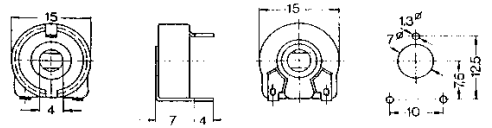
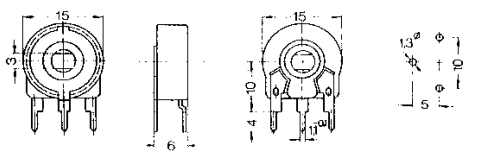


Schichtdrehwiderstand ($\geq$ 10.000 Betätigungen)

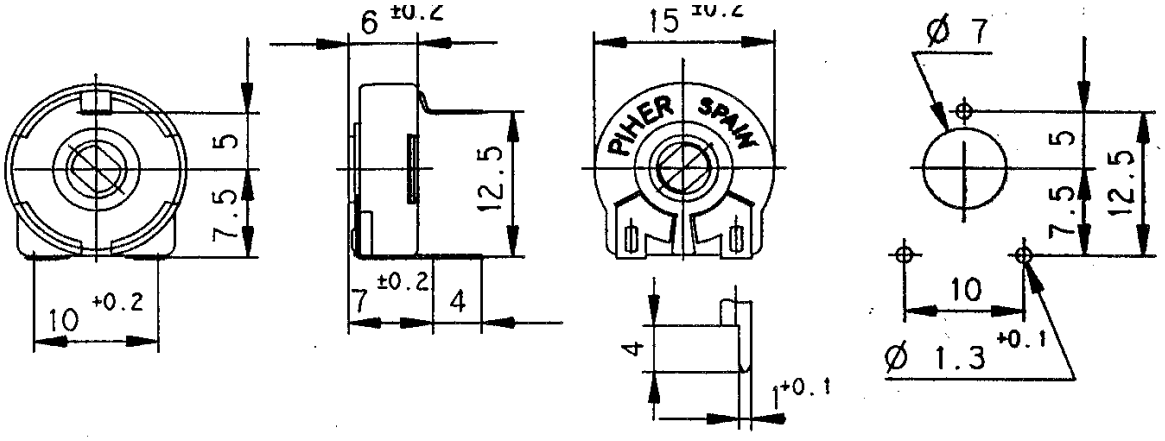
PT 15 Nv (12,5)



PT 15 Nh (5)



Abmessungen in mm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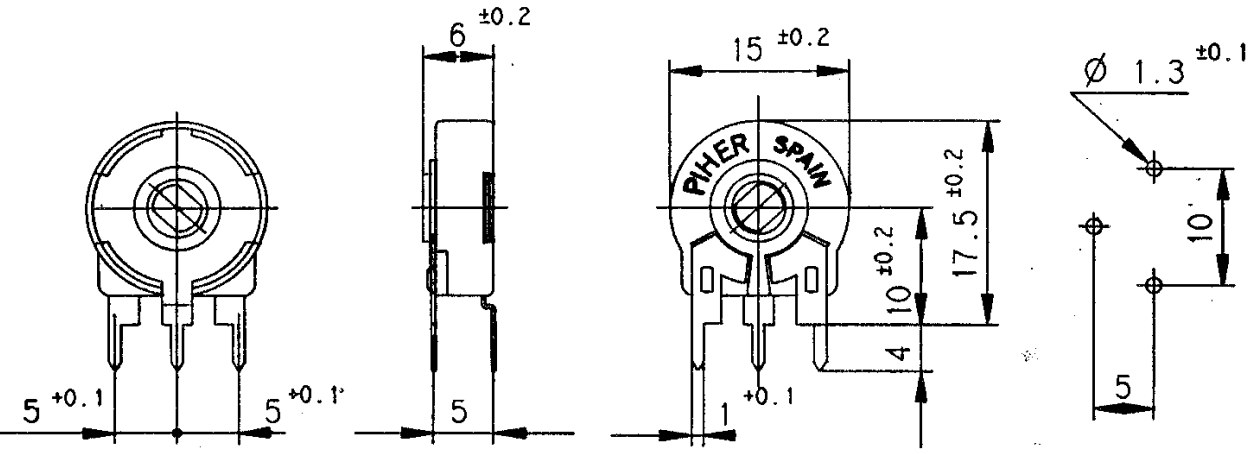
15 ±0.2
Ø 7
PIHER
SPAIN
5
7.5
12.5
10 +0.2
7 ±0.2
4
10
Ø 1.3 +0.1
1 +0.1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SPAIN
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10
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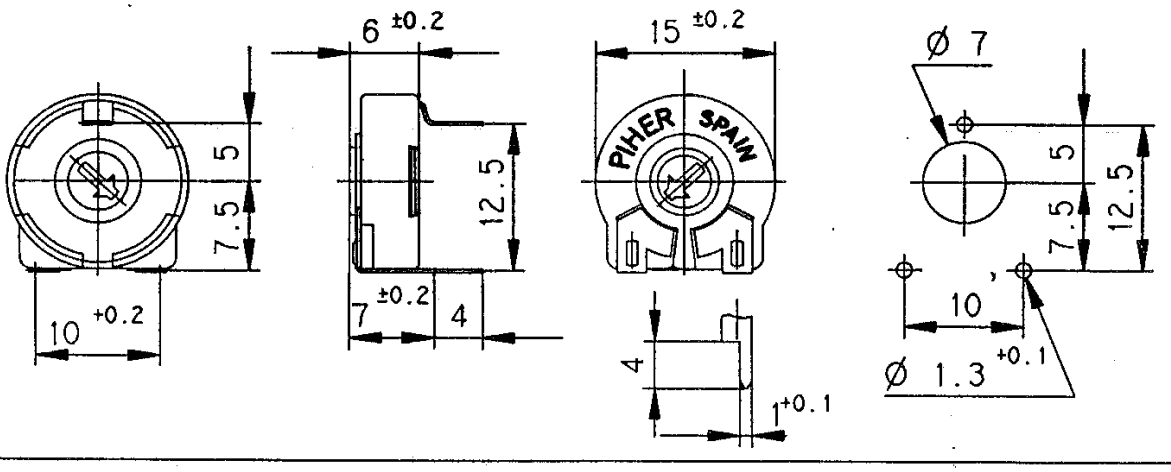
5 +0.1
5
1 +0.1
5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SPAIN
5
7.5
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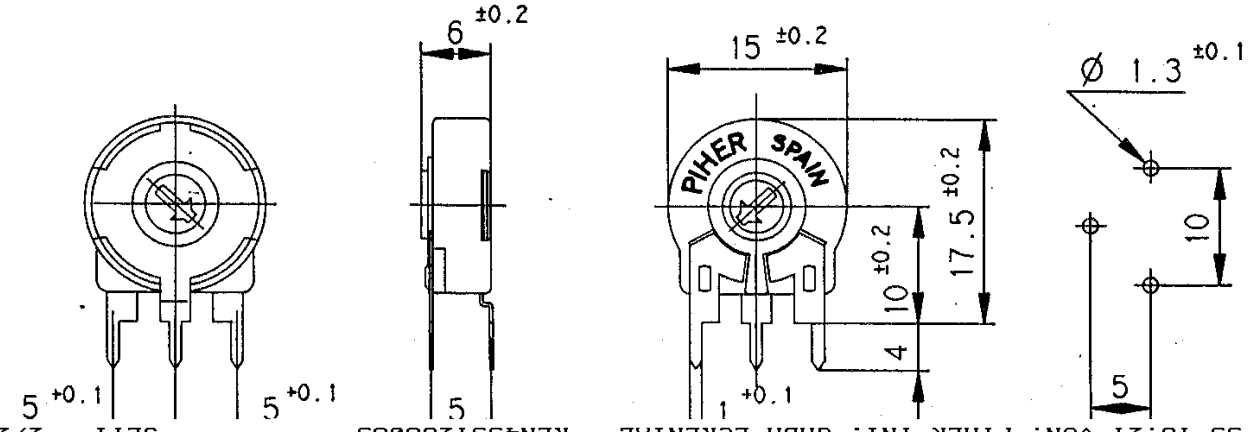
10 +0.2
7 ±0.2
4
10
Ø 1.3 +0.1
1 +0.1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SPAIN
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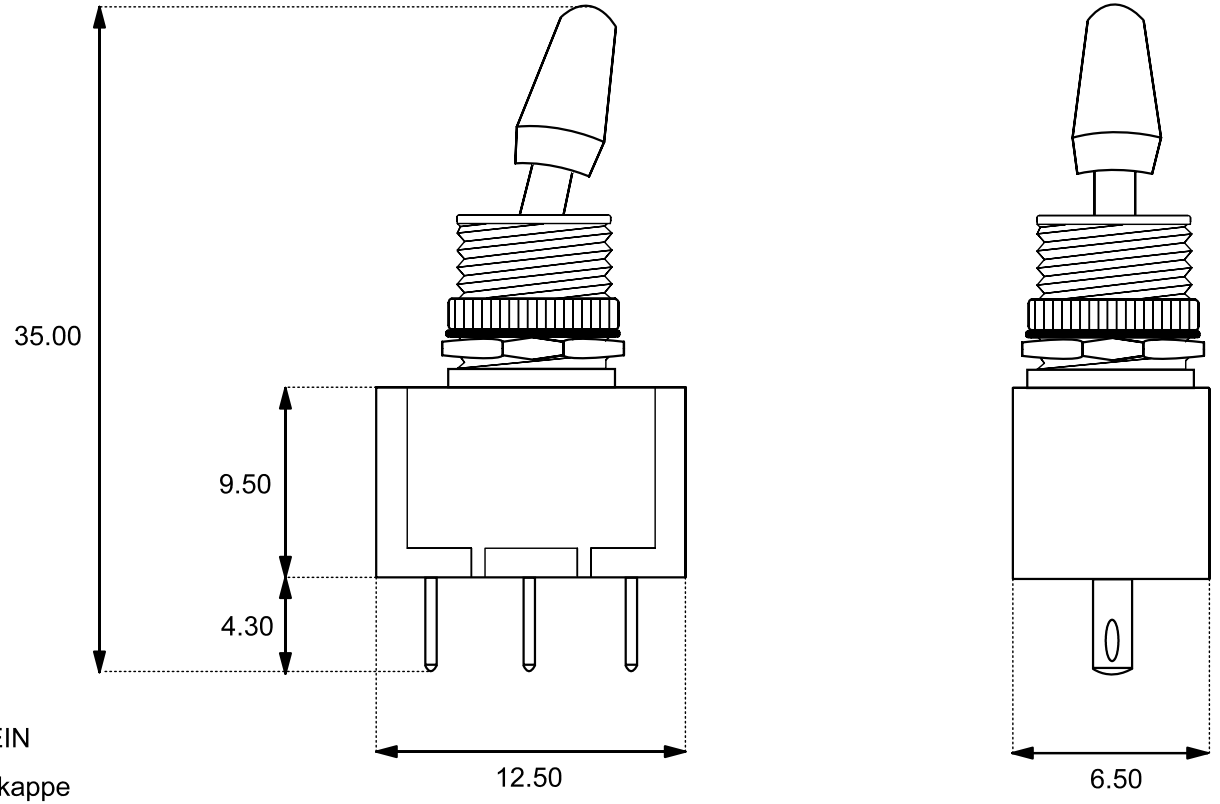


Kippschalter Miniatur, EIN-EIN

Metallhebel mit roter Plastikkappe

3 Pins - Lötösen

Nenn-Schaltstrom/-spannung 3A / 250V

Kontaktwiderstand < 0.01 Ohm

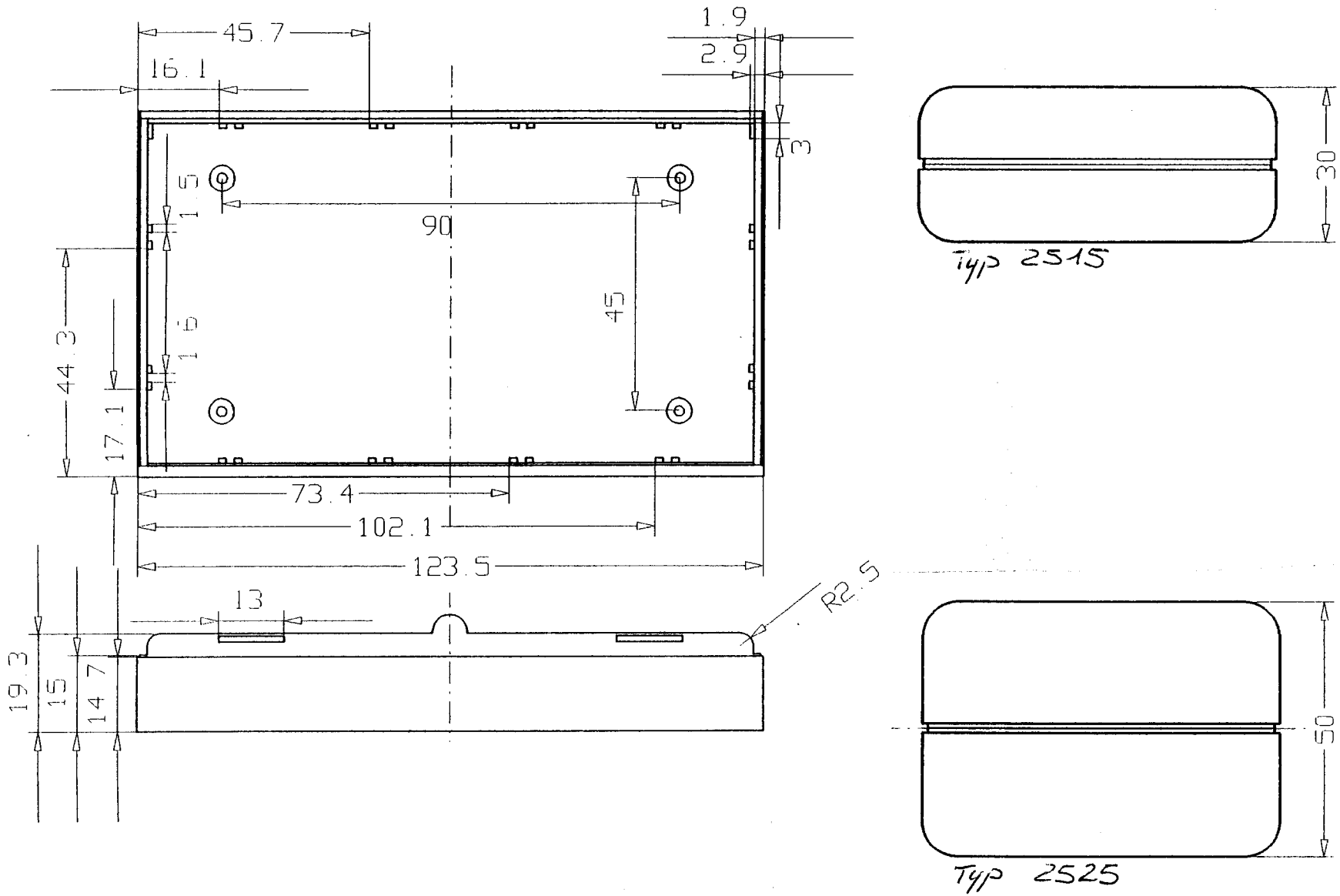
Isolationswiderstand >1500 MOhm

Spannungssicher bis 1500 VAC

Betätigungskraft 2-15 N

Gewinde M6x0.5

Änderungen			Datum	Name	Bezeichnung	Blattzahl:
Datum	Name	gez.:			KNX 1 10020	
		gepr.:				Blatt-Nr.:
					Zeichnungs-Nr.:	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15
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Typ 2515
50
Typ 2525